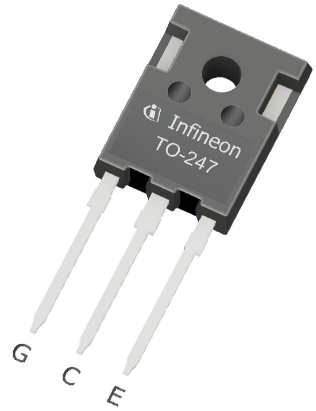
The TRENCHSTOP™ 5 WR6 family in the TO-247-3-HCC package offers improved reliability against package contamination

Features

- V_{CE} = 650 V
- I_C = 20 A
- Pin-to-pin creepage distance > 4.8 mm
- Pin-to-pin clearance distance > 3.4 mm
- Monolithic diode optimized for PFC and welding applications
- Stable temperature behavior
- Very low V_{CEsat} and low E_{off}
- Easy parallel switching capability based on positive temperature coefficient of V_{CEsat}
- Low temperature dependence of V_{CEsat} and E_{sw}
- Product spectrum and PSpice Models: http://www.infineon.com/igbt/



Lead-Free

Green

Halogen-Free

RoHS

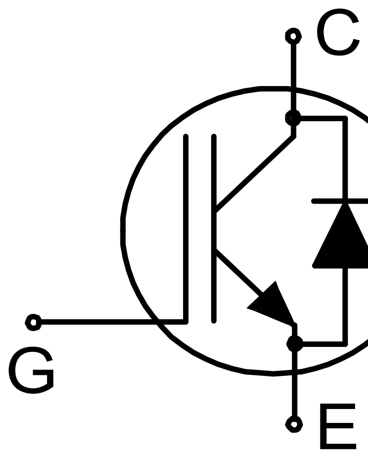
Potential applications

- PFC
- Welding
- ZCS applications

Product validation

- Product Validation: Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Description



Type	Package	Marking
IKWH20N65WR6	PG-TO247-3-HCC	H20EWR6

Table of contents

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in) from case	L_E			13.0		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature		wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque, M3 screw Maximum of mounting processes: 3	M				0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25$ °C		650	V
DC collector current, limited by T_{vjmax}	I_C		$T_C = 25$ °C	40	A
			$T_C = 100$ °C	20	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}			60	A
Turn-off safe operating area		$V_{CE} \leq$ 650 V, $t_P \leq$ 1 µs, $T_{vj} \leq$ 175 °C		60	A
Gate-emitter voltage	V_{GE}			±20	V
Transient gate-emitter voltage	V_{GE}	$t_p \leq$ 10 µs, $D < 0.010$		±20	V
Power dissipation	P_{tot}		$T_C = 25$ °C	140	W
			$T_C = 100$ °C	70	

Table 3 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter breakdown voltage	V_{BRCES}	$I_C = 0.2$ mA, $V_{GE} = 0$ V		650			V
Collector-emitter saturation voltage	$V_{CE\,sat}$	$I_C = 20.0$ A, $V_{GE} = 15$ V	$T_{vj} = 25$ °C		1.35	1.70	V
			$T_{vj} = 175$ °C		1.60		

Table 3 Characteristic values (continued)

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Gate-emitter threshold voltage	V_{GEth}	$I_C = 0.20$ mA, $V_{CE} = V_{GE}$		3.20	4.00	4.80	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 650$ V, $V_{GE} = 0$ V	$T_{vj} = 25$ °C			40	µA
			$T_{vj} = 175$ °C		0.5		mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0$ V, $V_{GE} = 20$ V				100	nA
Transconductance	g_{fs}	$I_C = 20.0$ A, $V_{CE} = 20$ V			50		S
Input capacitance	C_{ies}	$V_{CE} = 25$ V, $V_{GE} = 0$ V, $f = 100$ kHz			2130		pF
Output capacitance	C_{oes}	$V_{CE} = 25$ V, $V_{GE} = 0$ V, $f = 100$ kHz			22		pF
Reverse transfer capacitance	C_{res}	$V_{CE} = 25$ V, $V_{GE} = 0$ V, $f = 100$ kHz			9		pF
Gate charge	Q_G	$I_C = 20.0$ A, $V_{GE} = 15$ V, $V_{CE} = 520$ V			89		nC
Turn-on delay time	t_{don}	$V_{CE} = 400$ V, $V_{GE} = 15$ V, $R_{Gon} = 24.0$ Ω, $R_{Goff} = 24.0$ Ω, $L_\sigma = 30$ nH, $C_\sigma = 11$ pF	$T_{vj} = 25$ °C, $I_C = 20.0$ A		25		ns
			$T_{vj} = 175$ °C, $I_C = 20.0$ A		22		
Rise time (inductive load)	t_r	$V_{CE} = 400$ V, $V_{GE} = 15$ V, $R_{Gon} = 24.0$ Ω, $R_{Goff} = 24.0$ Ω, $L_\sigma = 30$ nH, $C_\sigma = 11$ pF	$T_{vj} = 25$ °C, $I_C = 20.0$ A		13		ns
			$T_{vj} = 175$ °C, $I_C = 20.0$ A		15		
Turn-off delay time	t_{doff}	$V_{CE} = 400$ V, $V_{GE} = 15$ V, $R_{Gon} = 24.0$ Ω, $R_{Goff} = 24.0$ Ω, $L_\sigma = 30$ nH, $C_\sigma = 11$ pF	$T_{vj} = 25$ °C, $I_C = 20.0$ A		255		ns
			$T_{vj} = 175$ °C, $I_C = 20.0$ A		290		
Fall time (inductive load)	t_f	$V_{CE} = 400$ V, $V_{GE} = 15$ V, $R_{Gon} = 24.0$ Ω, $R_{Goff} = 24.0$ Ω, $L_\sigma = 30$ nH, $C_\sigma = 11$ pF	$T_{vj} = 25$ °C, $I_C = 20.0$ A		17		ns
			$T_{vj} = 175$ °C, $I_C = 20.0$ A		17		
Turn-on energy	E_{on}	$V_{CE} = 400$ V, $V_{GE} = 15$ V, $R_{Gon} = 24.0$ Ω, $R_{Goff} = 24.0$ Ω, $L_\sigma = 30$ nH, $C_\sigma = 11$ pF	$T_{vj} = 25$ °C, $I_C = 20.0$ A		0.50		mJ
			$T_{vj} = 175$ °C, $I_C = 20.0$ A		0.62		
Turn-off energy	E_{off}	$V_{CE} = 400$ V, $V_{GE} = 15$ V, $R_{Gon} = 24.0$ Ω, $R_{Goff} = 24.0$ Ω, $L_\sigma = 30$ nH, $C_\sigma = 11$ pF	$T_{vj} = 25$ °C, $I_C = 20.0$ A		0.20		mJ
			$T_{vj} = 175$ °C, $I_C = 20.0$ A		0.35		

Table 3 Characteristic values (continued)

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Total switching energy	E_{ts}	V_{CE} = 400 V, V_{GE} = 15 V, R_{Gon} = 24.0 Ω, R_{Goff} = 24.0 Ω, $L_σ$ = 30 nH, $C_σ$ = 11 pF	T_{vj} = 25 °C, I_C = 20.0 A		0.70		mJ
			T_{vj} = 175 °C, I_C = 20.0 A		0.97		
IGBT thermal resistance, junction-case	R_{thjc}					1.10	K/W
Operating junction temperature	T_{vj}			-40		175	°C

Note: Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified.

3 Diode

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}	T_{vj} ≥ 25 °C		650	V
Diode forward current, limited by T_{vjmax}	I_F		T_C = 25 °C	17	A
			T_C = 100 °C	10	
Diode pulsed current, limited by T_{vjmax}	I_{Fpuls}			30	A

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode forward voltage	V_F	I_F = 8.5 A	T_{vj} = 25 °C		1.30	1.60	V
			T_{vj} = 175 °C		1.35		
Diode reverse recovery time	t_{rr}	V_R = 400 V	T_{vj} = 25 °C, I_F = 10.0 A, $-di_F/dt$ = 1340 A/µs		89		ns
			T_{vj} = 175 °C, I_F = 10.0 A, $-di_F/dt$ = 1300 A/µs		92		

Table 5 Characteristic values (continued)

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode reverse recovery charge	Q_{rr}	V_R = 400 V	T_{vj} = 25 °C, I_F = 10.0 A, $-di_F/dt$ = 1340 A/µs		1.00		µC
			T_{vj} = 175 °C, I_F = 10.0 A, $-di_F/dt$ = 1300 A/µs		1.70		
Diode peak reverse recovery current	I_{rrm}	V_R = 400 V	T_{vj} = 25 °C, I_F = 10.0 A, $-di_F/dt$ = 1340 A/µs		23.0		A
			T_{vj} = 175 °C, I_F = 10.0 A, $-di_F/dt$ = 1300 A/µs		29.1		
Diode peak rate off fall of reverse recovery current	dI_{rr}/dt	V_R = 400 V	T_{vj} = 25 °C, I_F = 10.0 A, $-di_F/dt$ = 1340 A/µs		-3328		A/µs
			T_{vj} = 175 °C, I_F = 10.0 A, $-di_F/dt$ = 1300 A/µs		-775		
Diode thermal resistance, junction-case	R_{thjc}					4.70	K/W
Operating junction temperature	T_{vj}			-40		175	°C

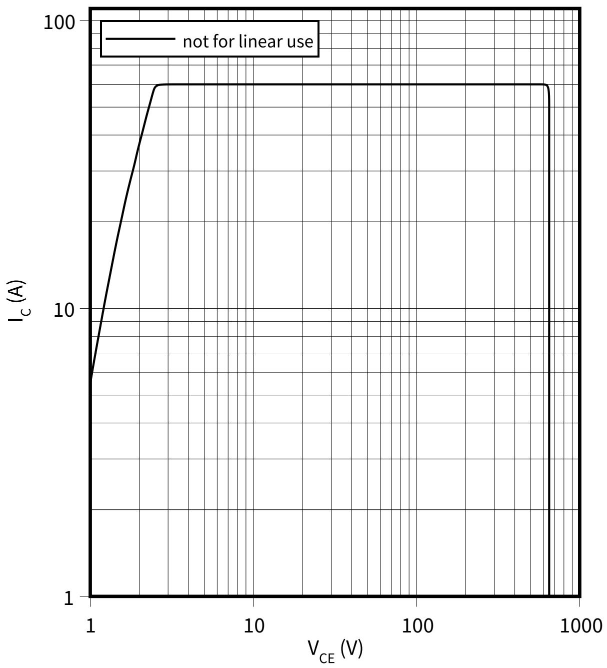
Note: *For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.*

4 Characteristics diagrams

Forward bias safe operating area, IGBT

$I_C = f(V_{CE})$

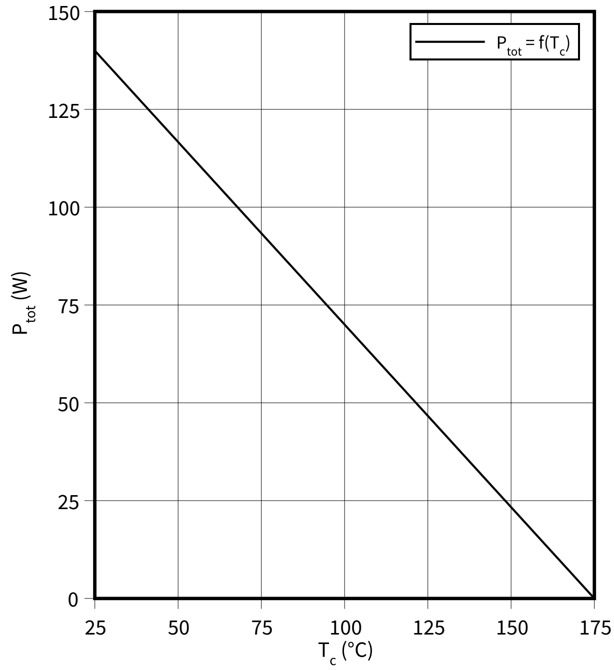
$t_p = 1\ \mu s$, $D = 0$, $T_{vj} \leq 175\ °C$, $T_C = 25\ °C$, $V_{GE} = 15\ V$



Power dissipation as a function of case temperature, IGBT

$P_{tot} = f(T_c)$

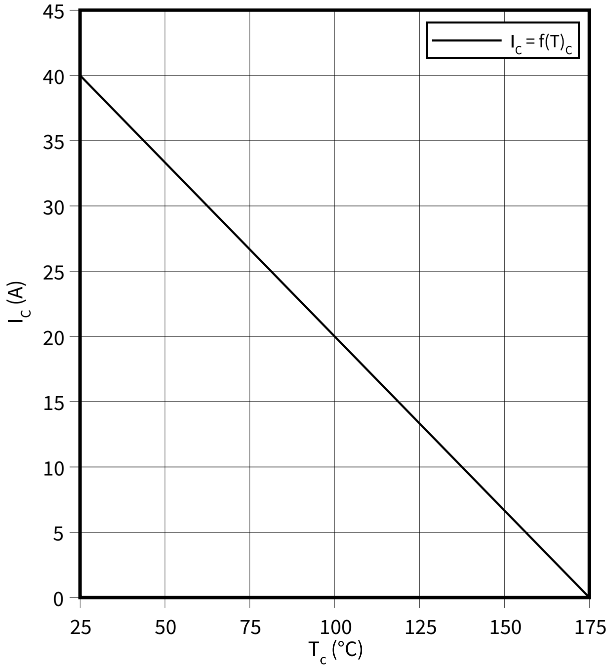
$T_{vj} \leq 175\ °C$



Collector current as a function of case temperature, IGBT

$I_C = f(T_c)$

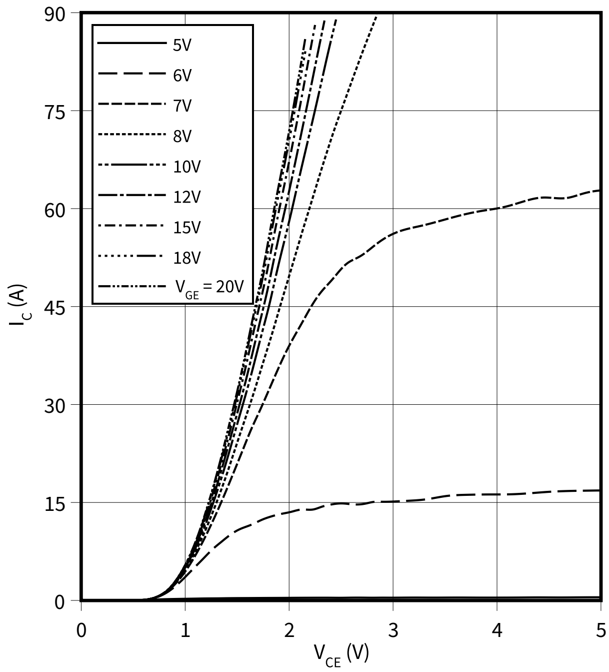
$T_{vj} \leq 175\ °C$, $V_{GE} \geq 15\ V$



Typical output characteristic, IGBT

$I_C = f(V_{CE})$

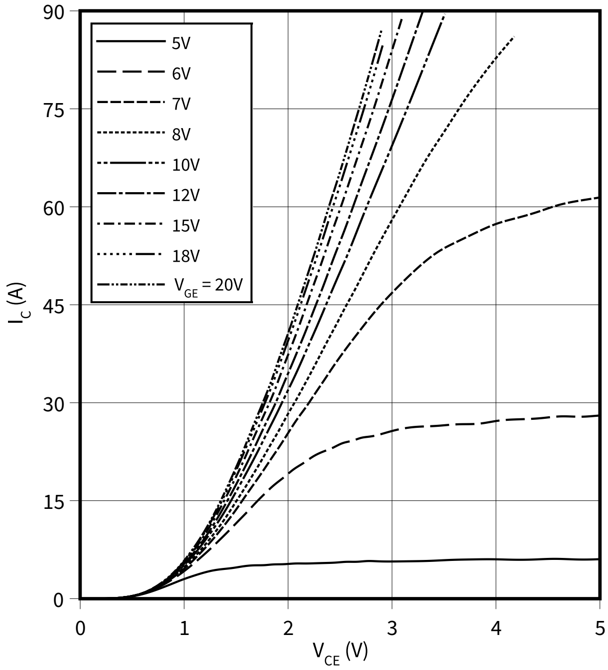
$T_{vj} = 25\ °C$



Typical output characteristic, IGBT

$I_C = f(V_{CE})$

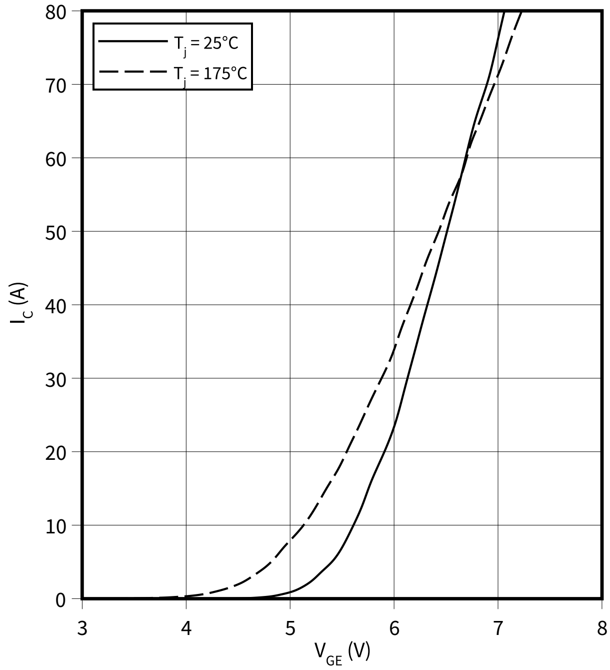
$T_{vj} = 175\ °C$



Typical transfer characteristic, IGBT

$I_C = f(V_{GE})$

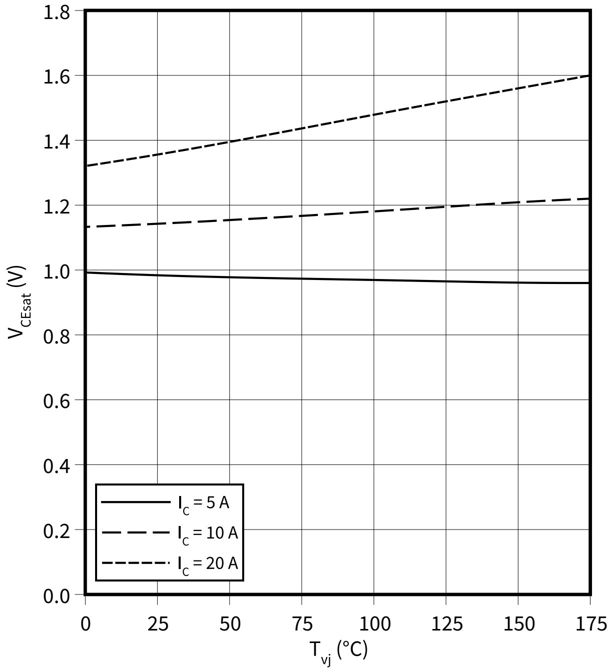
$V_{CE} = 20\ V$



Typical collector-emitter saturation voltage as a function of junction temperature, IGBT

$V_{CEsat} = f(T_{vj})$

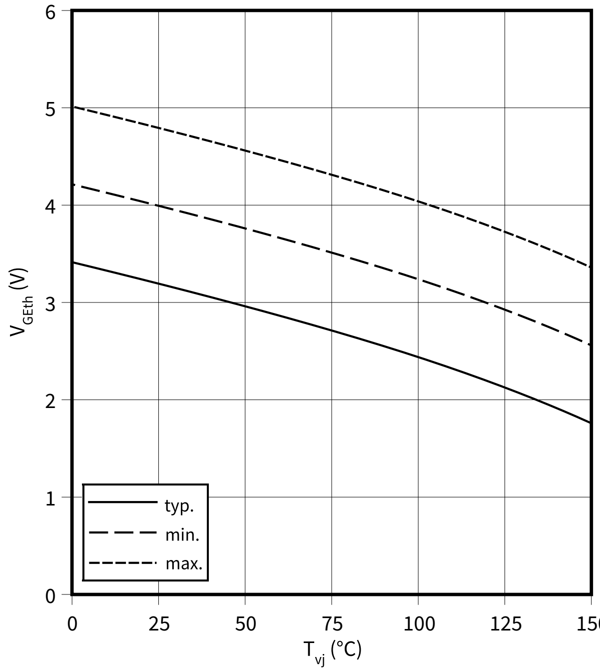
$V_{GE} = 15\ V$



Gate-emitter threshold voltage as a function of junction temperature, IGBT

$V_{GEth} = f(T_{vj})$

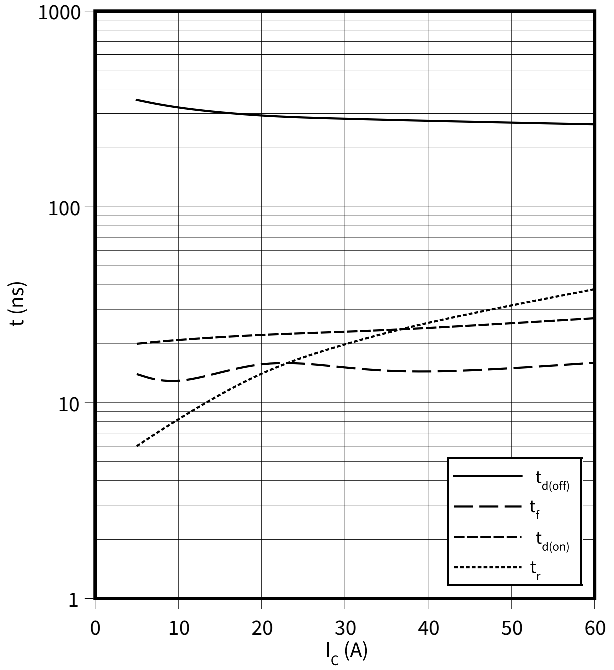
$I_C = 0.20\ mA$



Typical switching times as a function of collector current, IGBT

$t = f(I_C)$

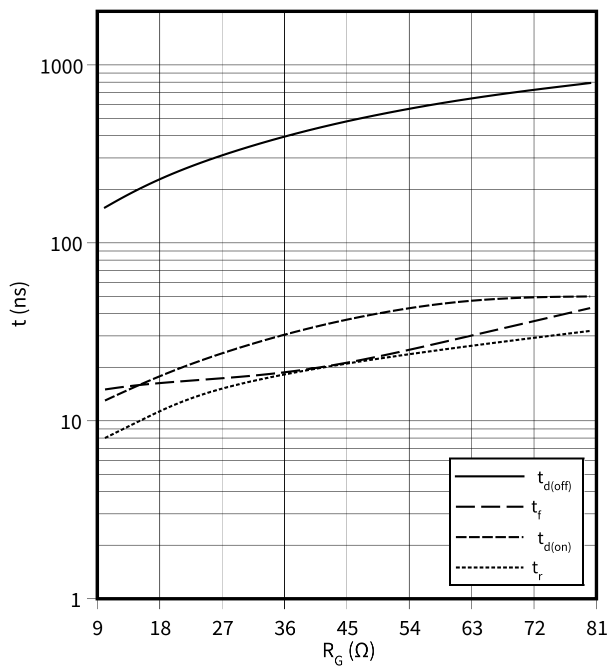
$V_{CE} = 400$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V, $R_G = 24$ Ω



Typical switching times as a function of gate resistor, IGBT

$t = f(R_G)$

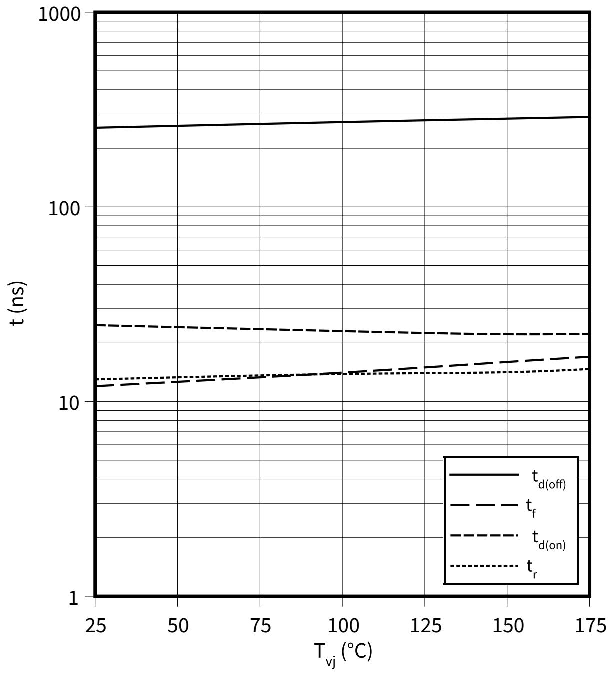
$I_C = 20.0$ A, $V_{CE} = 400$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V



Typical switching times as a function of junction temperature, IGBT

$t = f(T_{vj})$

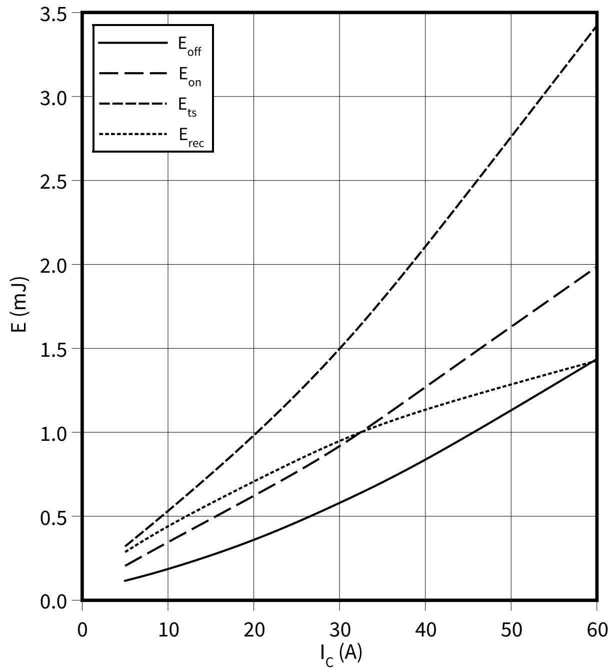
$I_C = 20.0$ A, $V_{CE} = 400$ V, $V_{GE} = 0/15$ V, $R_G = 24$ Ω



Typical switching energy losses as a function of collector current, IGBT

$E = f(I_C)$

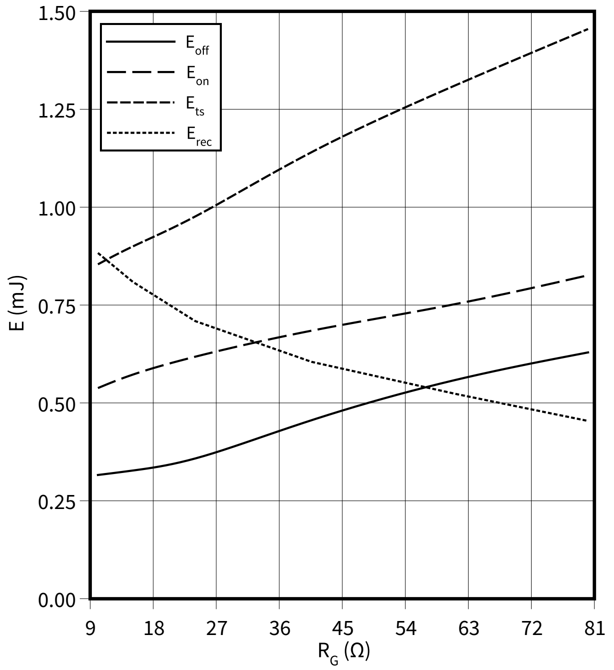
$V_{CE} = 400$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V, $R_G = 24$ Ω



Typical switching energy losses as a function of gate resistor, IGBT

$E = f(R_G)$

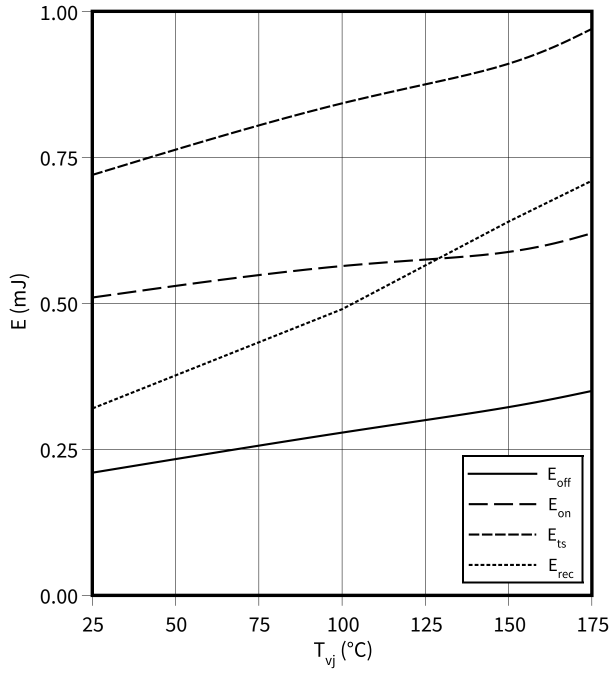
I_C = 20.0 A, V_{CE} = 400 V, T_{vj} = 175 °C, V_{GE} = 0/15 V



Typical switching energy losses as a function of junction temperature, IGBT

$E = f(T_{vj})$

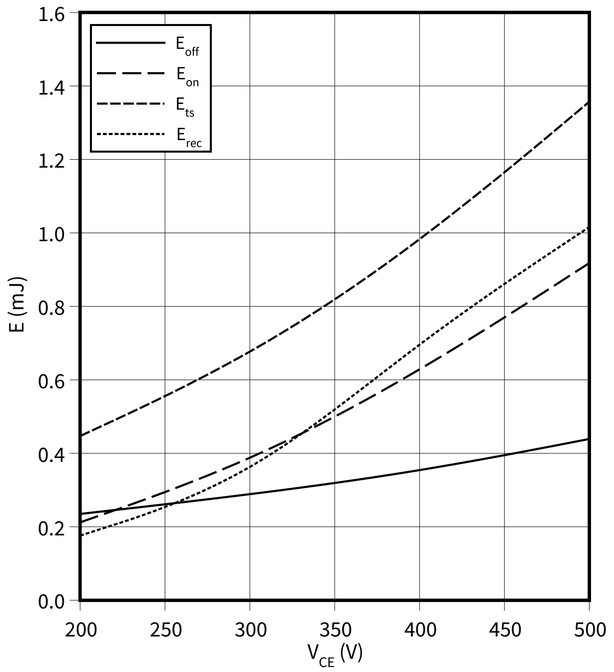
I_C = 20.0 A, V_{CE} = 400 V, V_{GE} = 0/15 V, R_G = 24 Ω



Typical switching energy losses as a function of collector emitter voltage, IGBT

$E = f(V_{CE})$

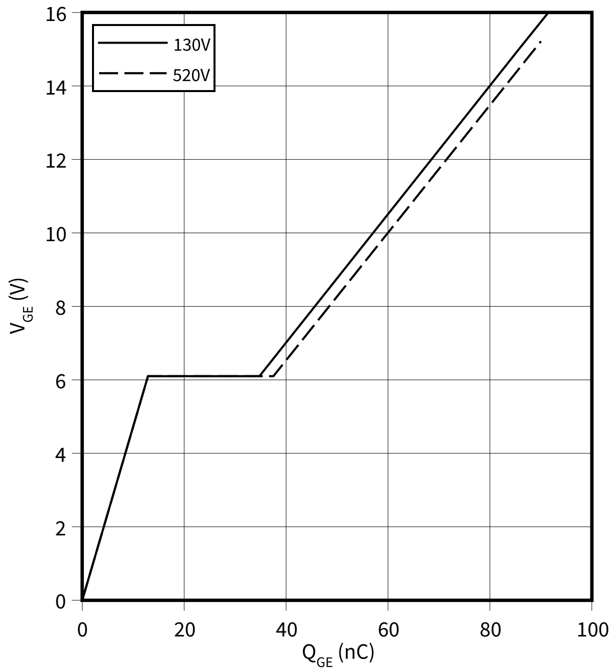
I_C = 20.0 A, T_{vj} = 175 °C, V_{GE} = 0/15 V, R_G = 24 Ω



Typical gate charge, IGBT

$V_{GE} = f(Q_{GE})$

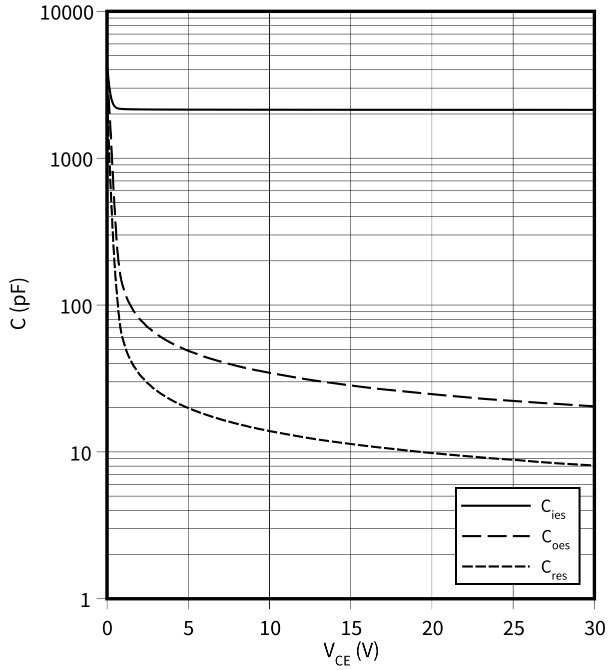
I_C = 20.0 A



Typical capacitance as a function of collector-emitter voltage, IGBT

$C = f(V_{CE})$

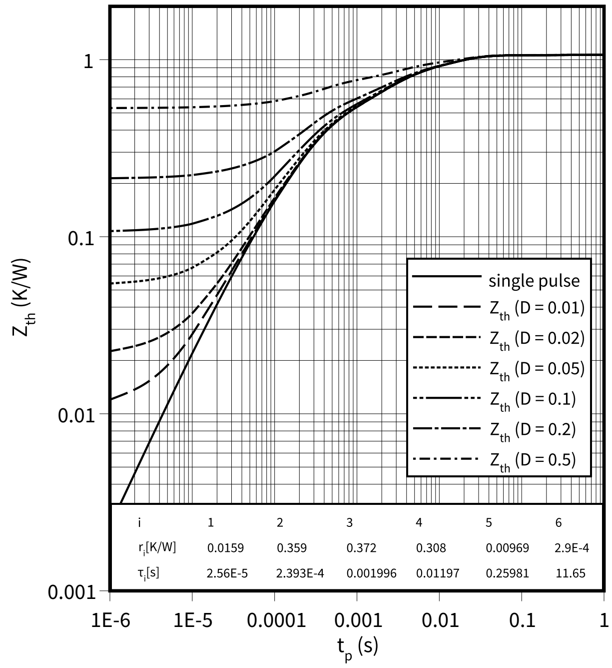
$f = 100\ kHz, V_{GE} = 0\ V$



IGBT transient thermal impedance as a function of pulse width, IGBT

$Z_{th} = f(t_p)$

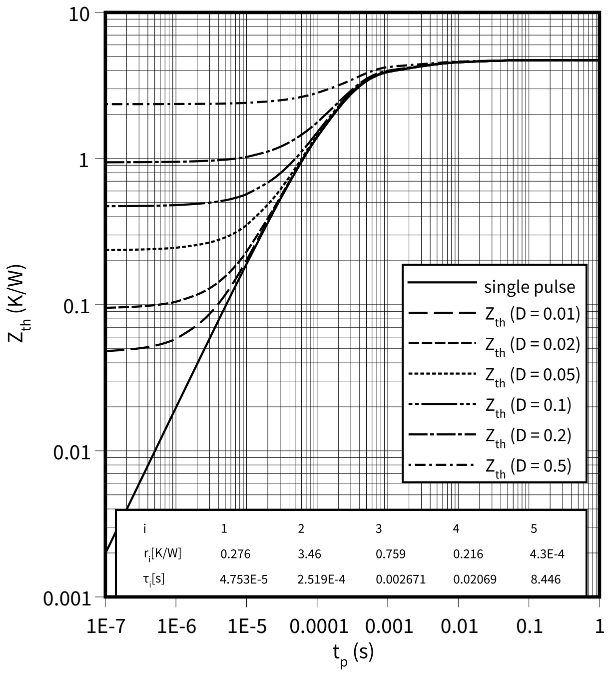
$D = t_p/T$



Diode transient thermal impedance as a function of pulse width, Diode

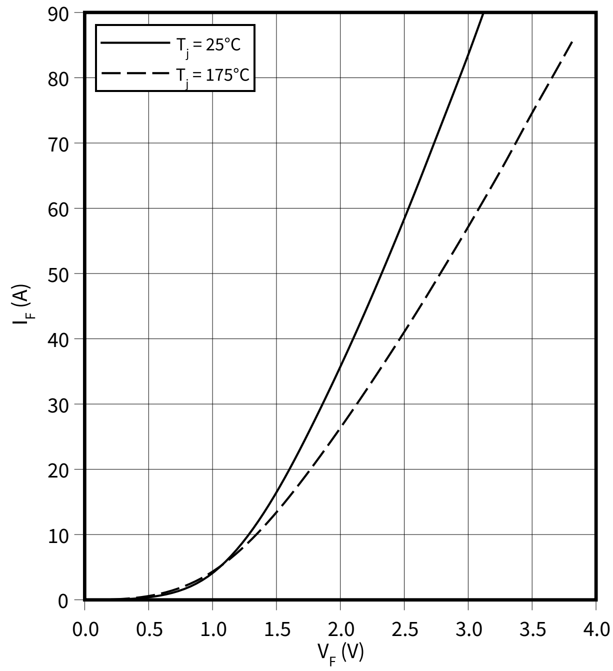
$Z_{th} = f(t_p)$

$D = t_p/T$



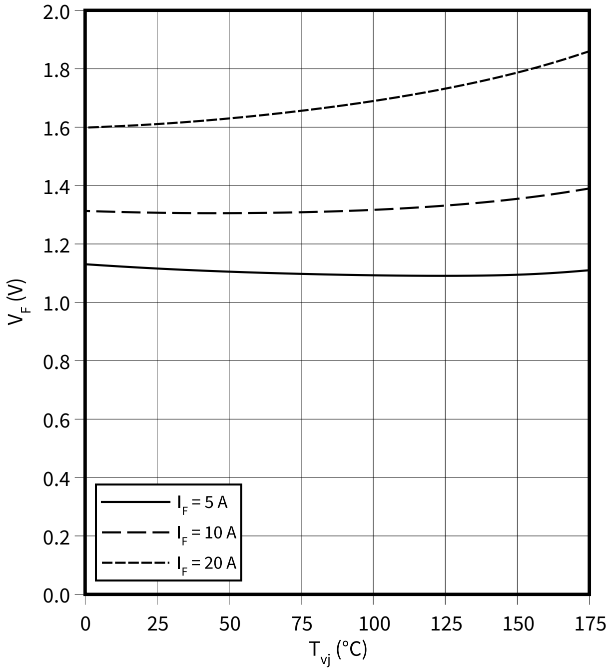
Typical diode forward current as a function of forward voltage, Diode

$I_F = f(V_F)$



Typical diode forward voltage as a function of junction temperature, Diode

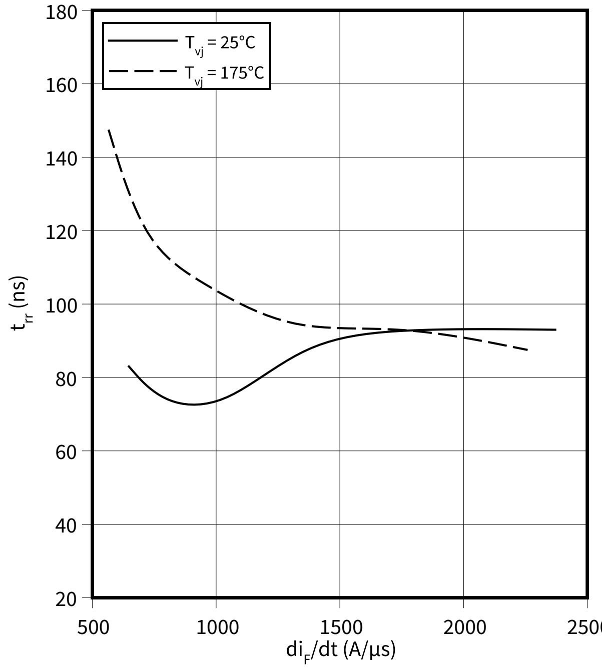
$V_F = f(T_{vj})$



Typical reverse recovery time as a function of diode current slope, Diode

$t_{rr} = f(di_F/dt)$

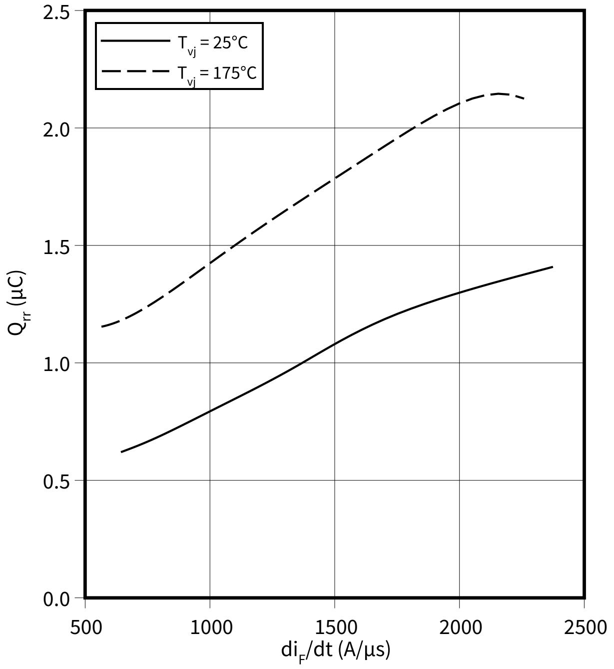
$V_R = 400$ V, $I_F = 10$ A



Typical reverse recovery charge as a function of diode current slope, Diode

$Q_{rr} = f(di_F/dt)$

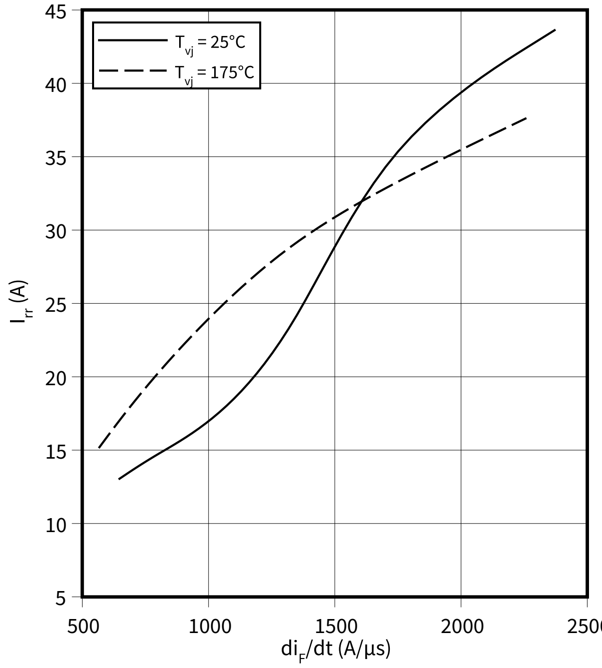
$V_R = 400$ V, $I_F = 10$ A



Typical reverse recovery current as a function of diode current slope, Diode

$I_{rr} = f(di_F/dt)$

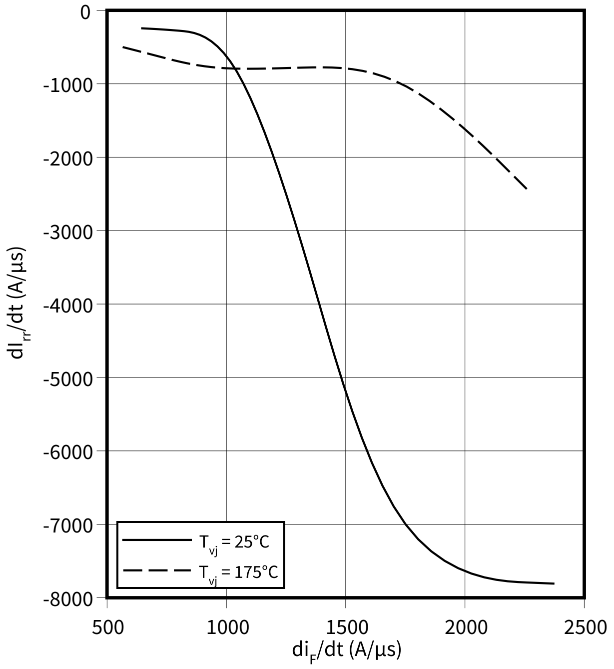
$V_R = 400$ V, $I_F = 10$ A



Typical diode peak rate of fall of reverse recovery current as a function of diode current slope, Diode

$dI_{rr}/dt = f(di_F/dt)$

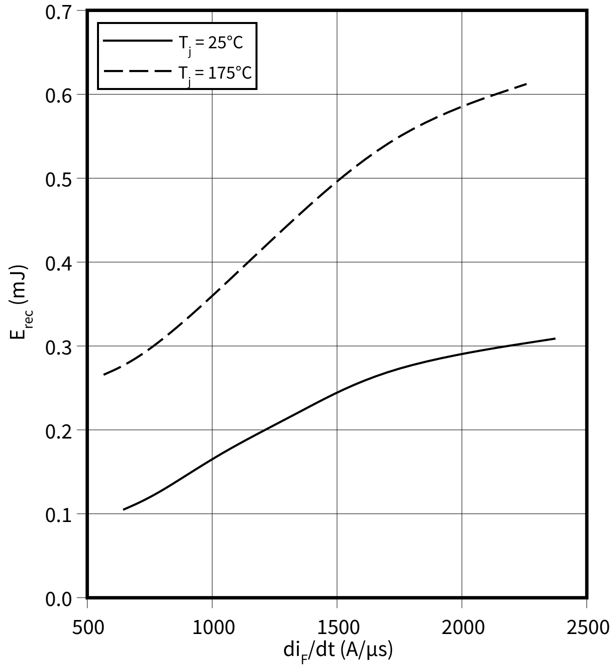
$V_R = 400\ V$, $I_F = 10\ A$



Typical reverse energy losses as a function of diode current slope, Diode

$E_{rec} = f(di_F/dt)$

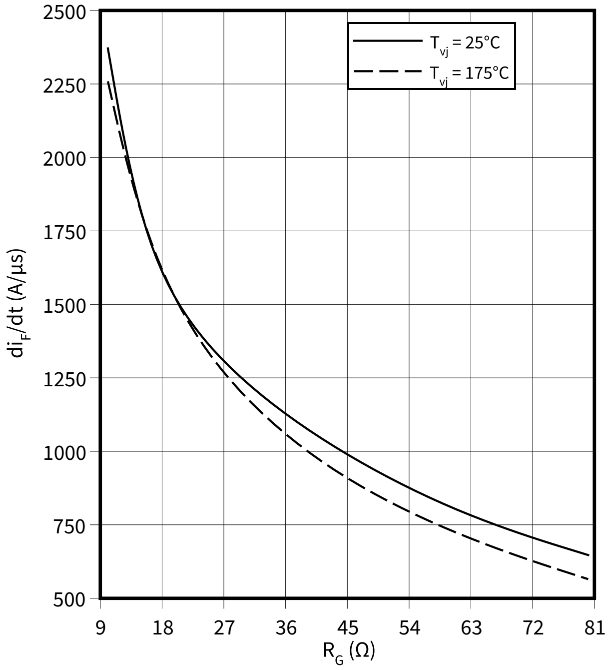
$V_R = 400\ V$, $I_F = 10\ A$



Typical diode current slope as a function of gate resistor, Diode

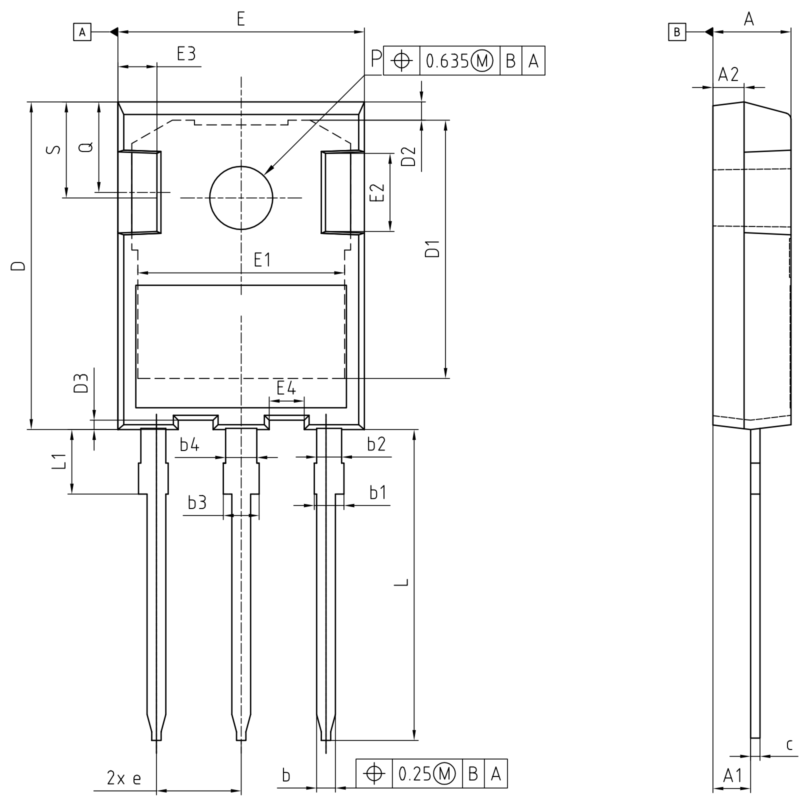
$di_F/dt = f(R_G)$

$V_R = 400\ V$, $I_F = 10\ A$



5 Package outlines

PG-TO247-3-HCC



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.48	2.02	0.058	0.080
b2	1.48	1.72	0.058	0.068
b3	1.84	2.42	0.072	0.095
b4	1.84	2.18	0.072	0.086
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
D3	0.55	0.65	0.022	0.026
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
E4	3.44	3.76	0.135	0.148
e	5.44 (BSC)		0.214 (BSC)	
L	19.80	20.32	0.780	0.800
L1	4.90	5.10	0.161	0.176
øP	2.40	2.60	0.138	0.146
Q	5.34	5.54	0.216	0.236
S	2.14	2.34	0.238	0.248
N	3		3	

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SCALE 3:1
0 1 2 3mm

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Figure 6

6 Testing conditions

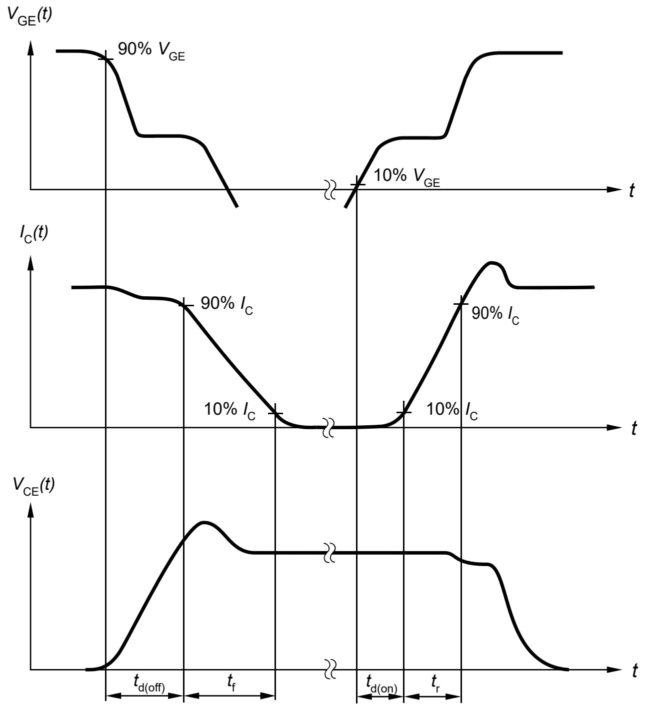

Figure A. **Definition of switching times**

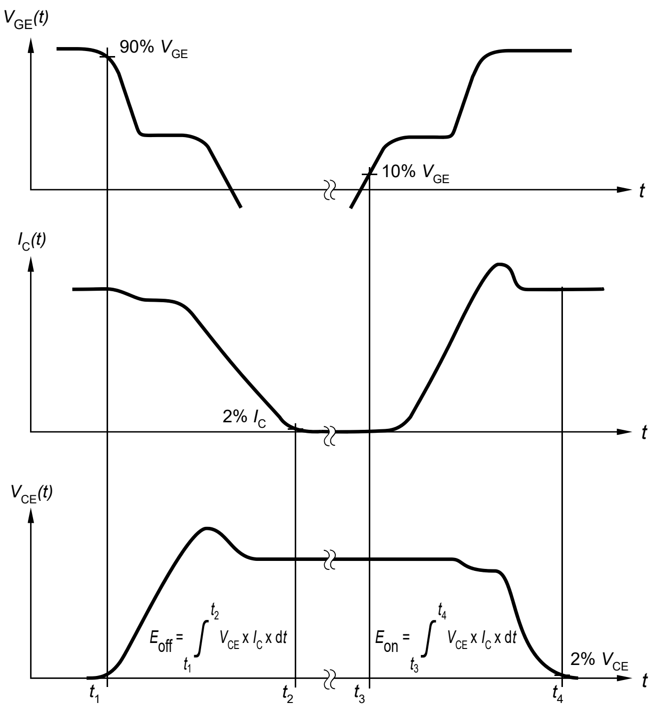

Figure B. **Definition of switching losses**

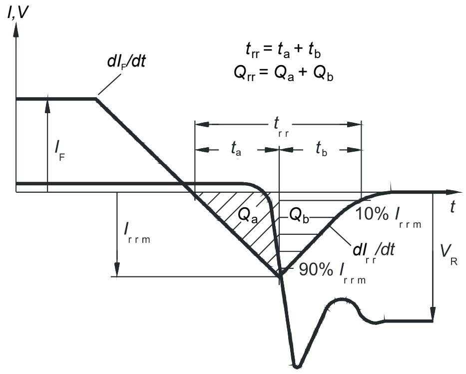

Figure C. **Definition of diode switching characteristics**

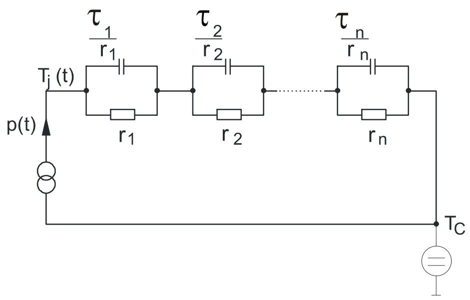

Figure D. **Thermal equivalent circuit**

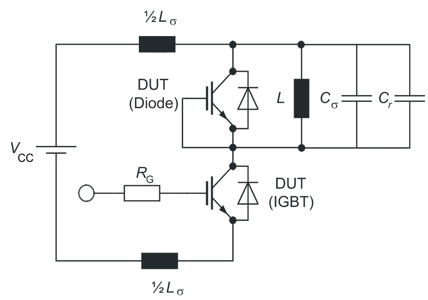

Figure E. **Dynamic test circuit**
Parasitic inductance L_{σ},
parasitic capacitor C_{σ},
relief capacitor C_{r},
(only for ZVT switching)

Figure 7

Revision history

Document revision	Date of release	Description of changes
1.00	2021-05-21	Final datasheet

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